

RIC7113E4

RADIATION HARDENED HIGH AND LOW SIDE GATE DRIVER

Features

- Total dose capability to 100 kRads(Si)
- Floating channel designed for bootstrap operation
- Fully operational to +400V
- Tolerant to negative transient voltage
- dV/dt immune
- Gate drive supply range from 10 to 20V
- Undervoltage lockout for both channels
- Separate logic supply range from 5 to 20V
Logic and power ground $\pm 5V$ offset
- CMOS Schmitt-triggered inputs with pull-down
- Cycle by cycle edge-triggered shutdown logic
- Matched propagation delay for both channels
- Outputs in phase with inputs
- Hermetically Sealed
- Lightweight
- ESD Rating: Class 1C per MIL-STD-883, Method 3015

Product Summary

V_{OFFSET}	400V max.
I_{O+/-}	2A / 2A
V_{OUT}	10 - 20V
t_{on/off} (typ.)	120 & 100 ns
Delay Matching(typ.)	5 ns

Description

The RIC7113E4 is a high voltage, high speed power MOSFET and IGBT driver with independent high and low side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. Logic inputs are compatible with standard CMOS or LSTTL outputs. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. Propagation delays are matched to simplify use in high frequency applications. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration which operates up to 400 volts.

Absolute Maximum Ratings

Absolute Maximum Ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The Thermal Resistance and Power Dissipation ratings are measured under board mounted and still air conditions.

Symbol	Parameter	Min.	Max.	Units
V _B	High Side Floating Supply Voltage	-0.5	V _S + 20	V
V _S	High Side Floating Supply Offset Voltage	—	400	
V _{HO}	High Side Floating Output Voltage	V _S - 0.5	V _B + 0.5	
V _{CC}	Low Side Fixed Supply Voltage	-0.5	20	
V _{LO}	Low Side Output Voltage	-0.5	V _{CC} + 0.5	
V _{DD}	Logic Supply Voltage	-0.5	V _{SS} + 20	
V _{SS}	Logic Supply Offset Voltage	V _{CC} - 20	V _{CC} + 0.5	
V _{IN}	Logic Input Voltage (HIN, LIN & SD)	V _{SS} - 0.5	V _{DD} + 0.5	
dV _S /dt	Allowable Offset Supply Voltage Transient (Figure 2)	—	50	V/ns
P _D	Package Power Dissipation @ T _{LEAD} ≤ +25°C	—	1.6	W
R _{thJC}	Thermal Resistance, Junction to Case	12 (Typ)	15.6	°C/W
R _{thJ-LEAD}	Thermal Resistance, Junction to Lead *	23 (Typ)	—	
R _{thJ-LID}	Thermal Resistance, Junction to Lid *	29 (Typ)	—	
T _J	Junction Temperature	-55	125	°C
T _S	Storage Temperature	-55	150	
T _L	Lead Temperature (Soldering, 10 seconds)	—	300	
	Weight	0.42(typical)		g

* Guaranteed by design, not tested

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The Input/Output logic timing diagram is shown in Figure 1. The V_S and V_{SS} offset ratings are tested with all supplies biased at 15V differential.

Symbol	Parameter	Min.	Max.	Units
V _B	High Side Floating Supply Absolute Voltage	V _S + 10	V _S + 20	V
V _S	High Side Floating Supply Offset Voltage	-4	400	
V _{HO}	High Side Floating Output Voltage	V _S	V _B	
V _{CC}	Low Side Fixed Supply Voltage	10	20	
V _{LO}	Low Side Output Voltage	0	V _{CC}	
V _{DD}	Logic Supply Voltage	V _{SS} + 5	V _{SS} + 20	
V _{SS}	Logic Supply Offset Voltage	-5	5	
V _{IN}	Logic Input Voltage (HIN, LIN & SD)	V _{SS}	V _{DD}	

VBIAS (V_{CC} , V_{BS} , V_{DD}) = 15V, and V_{SS} = COM unless otherwise specified. The dynamic electrical characteristics are measured using the test circuit shown in Figure 3.

		Tj = 25°C			Tj = -55 to 125°C			
Symbol	Parameter	Min.	Typ.	Max.	Min.	Max.	Units	Test Conditions
t _{on}	Turn-On Propagation Delay	—	120	150	—	260	ns	V _S = 0V
t _{off}	Turn-Off Propagation Delay	—	100	125	—	220		V _S = 400V
t _{sd}	Shutdown Propagation Delay	—	110	140	—	235		V _S = 400V
t _r	Turn-On Rise Time	—	25	35	—	50		C _L = 1000pf
t _f	Turn-Off Fall Time	—	17	25	—	40		C _L = 1000pf
MT	Delay Matching, HS & LS Turn-On/Off	—	5	20	—	—		H _{on} -L _{on} or H _{off} -L _{off}

Static Electrical Characteristics

V_{BIAS} (V_{CC}, V_{BS}, V_{DD}) = 15V, unless otherwise specified. The V_{IN}, V_{TH} and I_{IN} parameters are referenced to V_{SS} and are applicable to all three logic input pins: HIN, LIN and SD. The V_O and I_O parameters are referenced to COM or V_S and are applicable to the respective output pins: HO or LO.

Symbol	Parameter	T _j = 25°C		T _j = -55 to 125°C		Units	Test Conditions
		Min.	Max.	Min.	Max.		
V _{IH}	Logic "1" Input Voltage	3.1	—	3.3	—	V	V _{DD} = 5V
		6.4	—	6.8	—		V _{DD} = 10V
		9.5	—	10	—		V _{DD} = 15V
		12.5	—	13.3	—		V _{DD} = 20V
V _{IL}	Logic "0" Input Voltage	—	1.6	—	1.6	V	V _{DD} = 5V
		—	3.8	—	3.6		V _{DD} = 10V
		—	6.0	—	5.7		V _{DD} = 15V
		—	8.3	—	7.9		V _{DD} = 20V
V _{OH}	High Level Output Voltage, V _{BIAS} - V _O	—	1.2	—	1.5		V _{IN} = V _{IH} , I _O = 0A
V _{OL}	Low Level Output Voltage, V _O	—	0.1	—	0.1		V _{IN} = V _{IH} , I _O = 0A
I _{LK}	Offset Supply Leakage Current	—	50	—	250	μA	V _B = V _S = 400V
I _{QBS}	Quiescent V _{BS} Supply Current	—	230	—	500		V _{IN} = 0V, or V _{DD}
I _{QCC}	Quiescent V _{CC} Supply Current	—	340	—	600		V _{IN} = 0V, or V _{DD}
I _{QDD}	Quiescent V _{DD} Supply Current	—	30	—	60		V _{IN} = 0V, or V _{DD}
I _{IN+}	Logic "1" Input Bias Current	—	40	—	70		V _{IN} = V _{DD}
I _{IN-}	Logic "0" Input Bias Current	—	1.0	—	10		V _{IN} = 0V
V _{BSUV+}	V _{BS} Supply Undervoltage Positive Going Threshold	7.5	9.7	—	—	V	
V _{BSUV-}	V _{BS} Supply Undervoltage Negative Going Threshold	7.0	9.4	—	—		
V _{CCUV+}	V _{CC} Supply Undervoltage Positive Going Threshold	7.4	9.6	—	—		
V _{CCUV-}	V _{CC} Supply Undervoltage Negative Going Threshold	7.0	9.4	—	—		
I _{O+}	Output High Short Circuit Pulsed Current *	2.0	—	—	—	A	V _O = 0V, V _{IN} = V _{DD} PW ≤ 10 μs
I _{O-}	Output Low Short Circuit Pulsed Current *	2.0	—	—	—		V _O = 15V, V _{IN} = 0V PW ≤ 10 μs

* Guaranteed by design, not tested

Radiation Performance

International Rectifier Radiation Hardened gate drivers are tested to verify their hardness capability. The hardness assurance program at International Rectifier uses a Cobalt-60 (^{60}Co) source and heavy ion irradiation.

Every wafer shall be tested per MIL-STD-883, Method 1019, test condition A "Ionizing Radiation (Total Dose) Test Procedure".

Both pre- and post- irradiation performances are tested and specified using the same drive circuitry and test conditions to provide a direct comparison.

For Static Irradiation Test Conditions refer to figure 7.

Static Electrical Characteristics		T _j = 25°C		Units	Test Conditions
Symbol	Parameter	100K Rads (Si)			
		Min	Max		
V _{IH}	Logic “1” Input Voltage	3.1	—	V	VDD = 5V
		6.4	—		VDD = 10V
		9.5	—		VDD = 15V
		12.5	—		VDD = 20V
V _{IL}	Logic “0” Input Voltage	—	1.6	V	VDD = 5V
		—	3.8		VDD = 10V
			6.0		VDD = 15V
		—	8.3		VDD = 20V
V _{OH}	High Level Output Voltage, V _{BIAS} - V _O	—	1.2		V _{IN} =V _{IH} , I _O = 0A
V _{OL}	Low Level Output Voltage, V _O	—	0.1	V _{IN} =V _{IH} , I _O = 0A	
I _{LK}	Offset Supply Leakage Current	—	50	μA	VB =VS = 400V
I _{QBS}	Quiescent V _{BS} Supply Current	—	230		VIN =0V or VDD
I _{QCC}	Quiescent V _{CC} Supply Current	—	340		VIN =0V or VDD
I _{QDD}	Quiescent V _{DD} Supply Current	—	30		VIN =0V or VDD
I _{IN+}	Logic “1” Input Bias Current	—	40		VIN =VDD
I _{IN-}	Logic “0” Input Bias Current	—	1.0	VIN =0V	
V _{BSUV+}	V _{BS} Supply Undervoltage Positive Going Threshold	7.5	9.7	V	
V _{BSUV-}	V _{BS} Supply Undervoltage Negative Going Threshold	7.0	9.4		
V _{CCUV+}	V _{CC} Supply Undervoltage Positive Going Threshold	7.4	9.9		
V _{CCUV-}	V _{CC} Supply Undervoltage Negative Going Threshold	7.0	9.6		
I _{O+}	Output High Short Circuit Pulsed Current *	2.0	—	A	VO =0V, VIN =VDD PW ≤ 10 μs
I _{O-}	Output Low Short Circuit Pulsed Current *	2.0	—		VO =15V, VIN =0V PW ≤ 10 μs

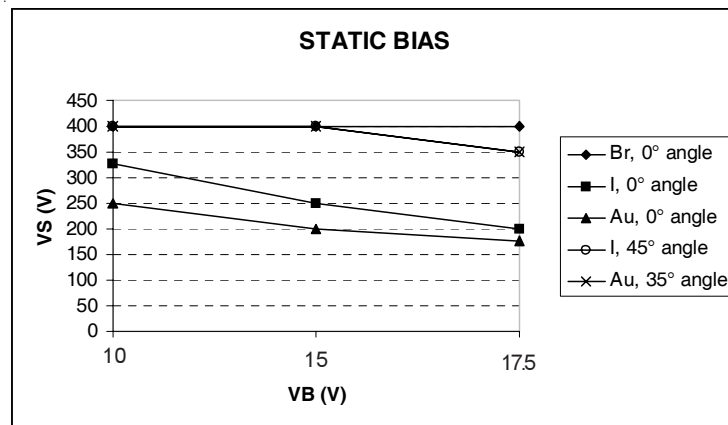
* Guaranteed by design, not tested

International Rectifier radiation hardened Gate Drivers have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization data is illustrated below. For Static Bias Test Conditions refer to figure 8.

Single Event Effect Safe Operating Area

Ion	LET MeV/(mg/cm ²)	Energy (MeV)	Angle (degrees)	V _s (V)		
				@ V _{BS} = 10V	@ V _{BS} = 15V	@ V _{BS} = 17.5V
Br	37	284	0	400	400	400
I	60	344	0	325	250	200
Au	82	346	0	250	200	175
I	85	344	45	400	400	350
Au	100	346	35	400	400	350

Note: VCC/VDD = 20V, except for LET=100, then VCC/VDD = 17.5V



Single Event Effect, Safe Operating Area

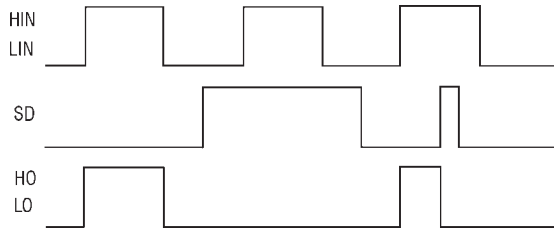


Figure 1. Input/Output Logic Timing Diagram

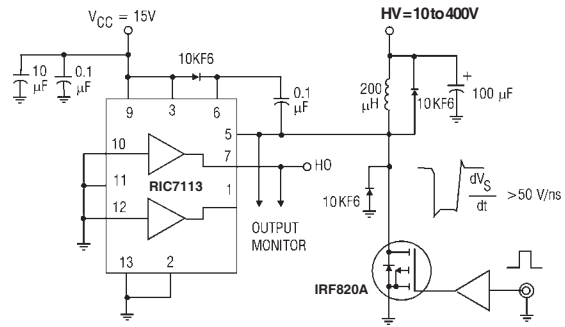


Figure 2. Floating Supply Voltage Transient Test Circuit

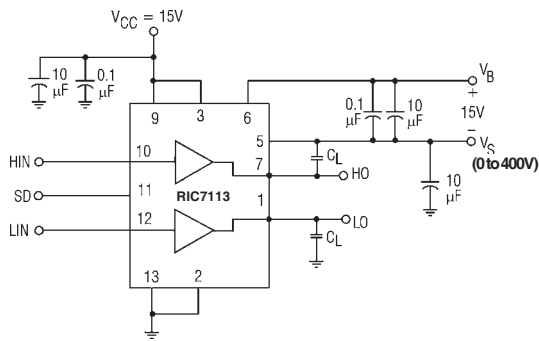


Figure 3. Switching Time Test Circuit

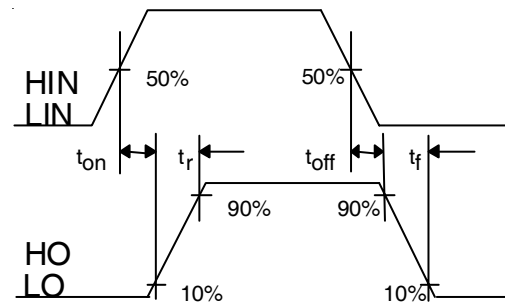


Figure 4. Switching Time Waveform Definition

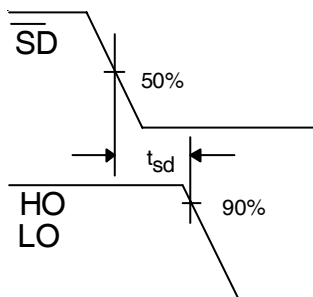


Figure 5. Shutdown Waveform Definitions

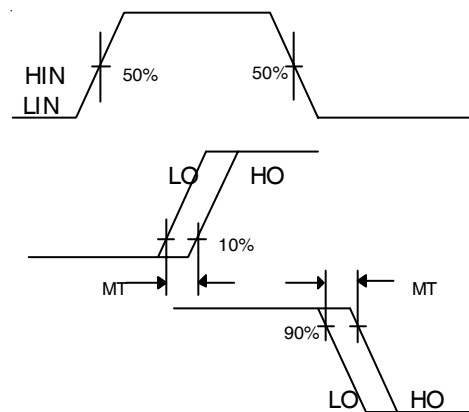


Figure 6. Delay Matching Waveform Definitions

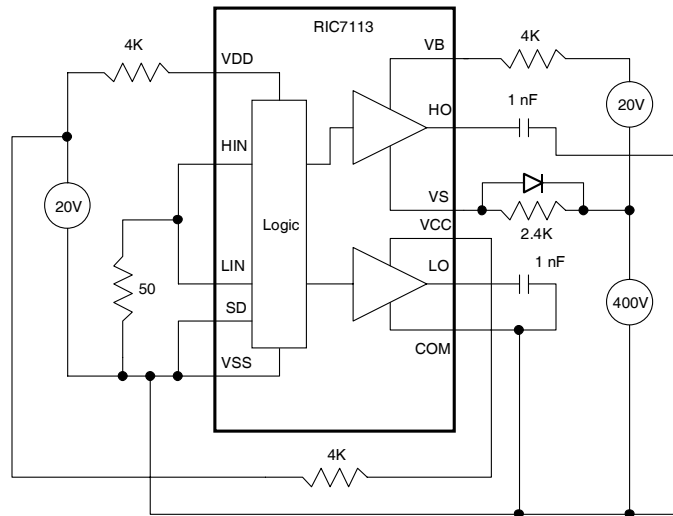


Figure 7. Static Bias Conditions for Total Ionizing Dose Test

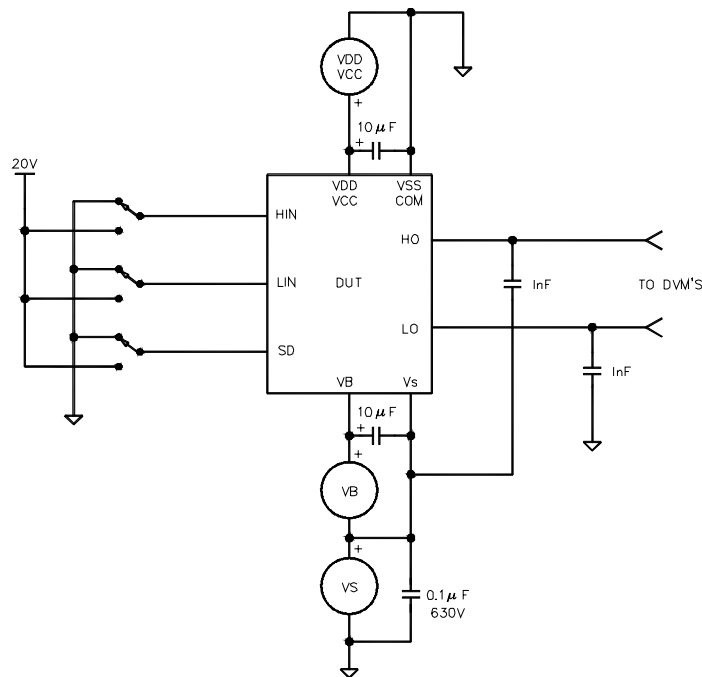
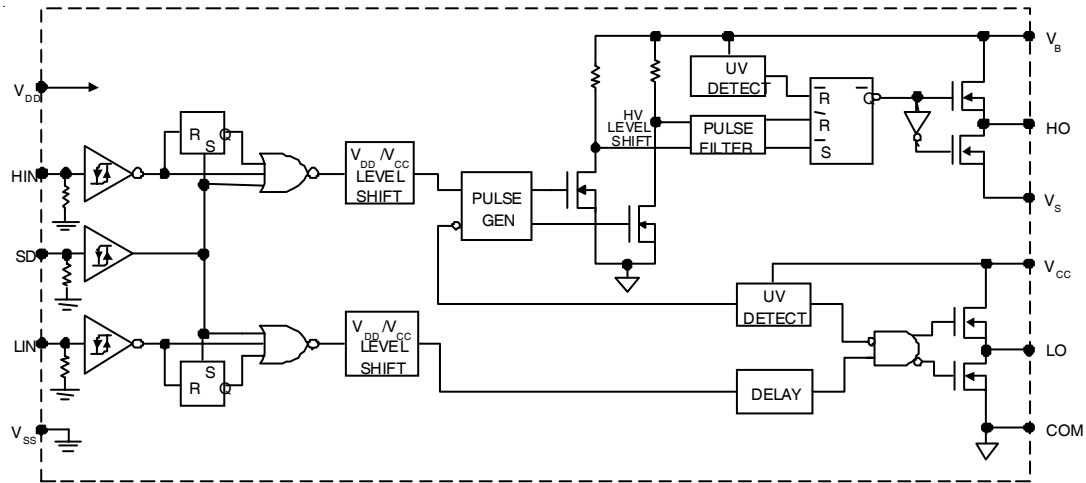


Figure 8. Static Bias Conditions for Single Event Effect Test

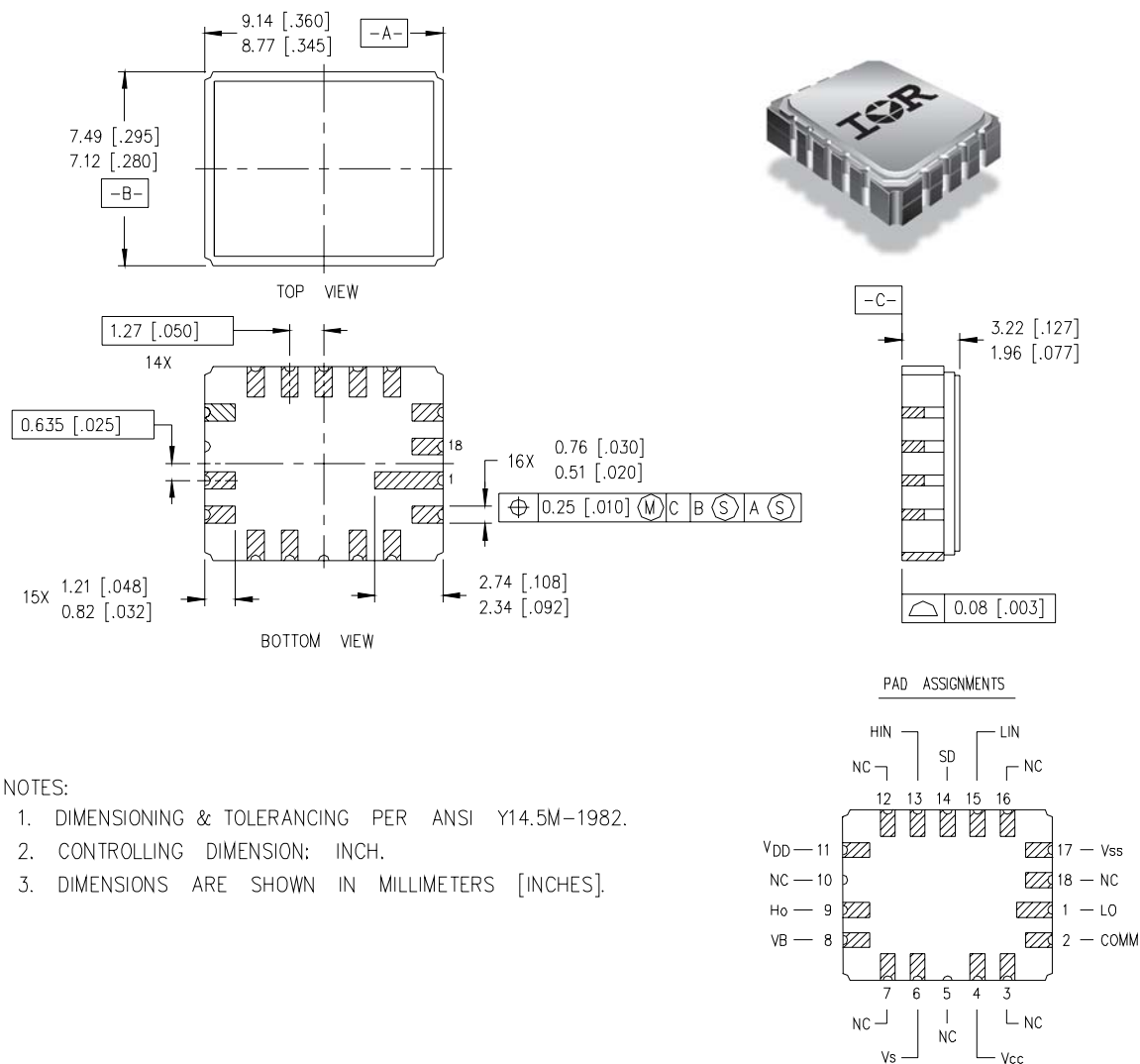
Functional Block Diagram



Lead Definitions

Symbol	Description
V _{DD}	Logic supply
HIN	Logic input for high side gate driver output (HO), in phase
SD	Logic input for shutdown
LIN	Logic input for low side gate driver output (LO), in phase
V _{SS}	Logic ground
V _B	High side floating supply
HO	High side gate drive output
V _S	High side floating supply return
V _{CC}	Low side supply
LO	Low side gate drive output
COM	Low side return

Case Outline and Dimensions — Leadless Chip Carrier (LCC-18) Package



NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].